

Helena Castañón

List of Publications by Year in descending order

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163
papers

1,534
citations

394286

19
h-index

414303

32
g-index

164
all docs

164
docs citations

164
times ranked

1357
citing authors

#	ARTICLE	IF	CITATIONS
1	Standards for the Characterization of Endurance in Resistive Switching Devices. ACS Nano, 2021, 15, 17214-17231.	7.3	128
2	A comparative study of the electrical properties of TiO ₂ films grown by high-pressure reactive sputtering and atomic layer deposition. Semiconductor Science and Technology, 2005, 20, 1044-1051.	1.0	79
3	Admittance spectroscopy in junctions. Solid-State Electronics, 1992, 35, 285-297.	0.8	74
4	Deposition of SiN _x :H thin films by the electron cyclotron resonance and its application to Al/SiN _x :H/Si structures. Journal of Applied Physics, 1998, 83, 332-338.	1.1	48
5	Influence of single and double deposition temperatures on the interface quality of atomic layer deposited Al ₂ O ₃ dielectric thin films on silicon. Journal of Applied Physics, 2006, 99, 054902.	1.1	47
6	Experimental observation of conductance transients in Al/SiN _x :H/Si metal-insulator-semiconductor structures. Applied Physics Letters, 1997, 71, 826-828.	1.5	45
7	Electrical characteristics of metal-insulator-semiconductor structures with atomic layer deposited Al ₂ O ₃ , HfO ₂ , and nanolaminates on different silicon substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 01AA07.	0.6	41
8	Electrical Properties of Atomic-Layer-Deposited Thin Gadolinium Oxide High-k Gate Dielectrics. Journal of the Electrochemical Society, 2007, 154, G207.	1.3	36
9	Experimental verification of intermediate band formation on titanium-implanted silicon. Journal of Applied Physics, 2013, 113, 024104.	1.1	33
10	The electrical-interface quality of as-grown atomic-layer-deposited disordered HfO ₂ on p- and n-type silicon. Semiconductor Science and Technology, 2004, 19, 1141-1148.	1.0	31
11	Optical admittance spectroscopy: A new method for deep level characterization. Journal of Applied Physics, 1987, 61, 2541-2545.	1.1	29
12	A physically based model for resistive memories including a detailed temperature and variability description. Microelectronic Engineering, 2017, 178, 26-29.	1.1	29
13	Interface quality study of ECR-deposited and rapid thermal annealed silicon nitride Al/SiN _x :H/InP and Al/SiN _x :H/In _{0.53} Ga _{0.47} As structures by DLTS and conductance transient techniques. Microelectronics Reliability, 2000, 40, 845-848.	0.9	26
14	Influence of interlayer trapping and detrapping mechanisms on the electrical characterization of hafnium oxide/silicon nitride stacks on silicon. Journal of Applied Physics, 2008, 104, .	1.1	25
15	Electrical characterization of atomic-layer-deposited hafnium oxide films from hafnium tetrakis(dimethylamide) and water/ozone: Effects of growth temperature, oxygen source, and postdeposition annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	25
16	Programming Pulse Width Assessment for Reliable and Low-Energy Endurance Performance in Al:HfO ₂ -Based RRAM Arrays. Electronics (Switzerland), 2020, 9, 864.	1.8	25
17	Effect of interlayer trapping and detrapping on the determination of interface state densities on high-k dielectric stacks. Journal of Applied Physics, 2010, 107, .	1.1	24
18	2 MeV electron irradiation effects on the electrical characteristics of metal-oxide-silicon capacitors with atomic layer deposited Al ₂ O ₃ , HfO ₂ and nanolaminated dielectrics. Solid-State Electronics, 2013, 79, 65-74.	0.8	23

#	ARTICLE	IF	CITATIONS
19	Conductance transient, capacitance-voltage and deep-level transient spectroscopy characterization of atomic layer deposited hafnium and zirconium oxide thin films. <i>Solid-State Electronics</i> , 2003, 47, 1623-1629.	0.8	21
20	Irradiation effect on dielectric properties of hafnium and gadolinium oxide gate dielectrics. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 416.	1.3	18
21	Electrical properties of thin zirconium and hafnium oxide high-k gate dielectrics grown by atomic layer deposition from cyclopentadienyl and ozone precursors. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 389.	1.3	18
22	Characterization of the damage induced in boron-implanted and RTA annealed silicon by the capacitance-voltage transient technique. <i>Semiconductor Science and Technology</i> , 1994, 9, 1637-1648.	1.0	17
23	Use of anodic tantalum pentoxide for high-density capacitor fabrication. <i>Journal of Materials Science: Materials in Electronics</i> , 1999, 10, 379-384.	1.1	17
24	Experimental observations of temperature-dependent flat band voltage transients on high-k dielectrics. <i>Microelectronics Reliability</i> , 2007, 47, 653-656.	0.9	17
25	Characterization of the DX centers in AlGaAs:Si by admittance spectroscopy. <i>Journal of Applied Physics</i> , 1991, 69, 4300-4305.	1.1	16
26	Electrical properties of high-pressure reactive sputtered thin hafnium oxide high-k gate dielectrics. <i>Semiconductor Science and Technology</i> , 2007, 22, 1344-1351.	1.0	16
27	Energy levels distribution in supersaturated silicon with titanium for photovoltaic applications. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	16
28	Good quality Al/SiNx:H/InP metal-insulator-semiconductor devices obtained with electron cyclotron resonance plasma method. <i>Journal of Applied Physics</i> , 1998, 83, 600-603.	1.1	15
29	Study From Cryogenic to High Temperatures of the High- and Low-Resistance-State Currents of ReRAM NiO ₂ /HfO ₂ /Si Capacitors. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 1877-1883.	1.6	15
30	Analysis and control of the intermediate memory states of RRAM devices by means of admittance parameters. <i>Journal of Applied Physics</i> , 2018, 124, .	1.1	15
31	Atomic layer deposition and properties of ZrO ₂ /Fe ₂ O ₃ thin films. <i>Beilstein Journal of Nanotechnology</i> , 2018, 9, 119-128.	1.5	15
32	Electrical characterization of high-k based metal-insulator-semiconductor structures with negative resistance effect when using Al ₂ O ₃ and nanolaminated films deposited on p-Si. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, 01A901.	0.6	14
33	Controlling the intermediate conductance states in RRAM devices for synaptic applications. <i>Microelectronic Engineering</i> , 2019, 215, 110984.	1.1	14
34	Electron thermal emission rates of nickel centers in silicon. <i>Solid-State Electronics</i> , 1986, 29, 883-884.	0.8	13
35	Effect of growth temperature and postmetallization annealing on the interface and dielectric quality of atomic layer deposited HfO ₂ on p and n silicon. <i>Journal of Applied Physics</i> , 2004, 96, 1365-1372.	1.1	13
36	Comparative study on electrical properties of atomic layer deposited high-permittivity materials on silicon substrates. <i>Thin Solid Films</i> , 2005, 474, 222-229.	0.8	13

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37	Influence of growth and annealing temperatures on the electrical properties of Nb ₂ O ₅ -based MIM capacitors. <i>Semiconductor Science and Technology</i> , 2013, 28, 055005.	1.0	13
38	Study of the admittance hysteresis cycles in TiN/Ti/HfO ₂ /W-based RRAM devices. <i>Microelectronic Engineering</i> , 2017, 178, 30-33.	1.1	13
39	Thermally induced improvements on SiN _x :H/InP devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999, 17, 2178-2182.	0.9	12
40	Atomic Layer Deposition and Properties of HfO ₂ -Al ₂ O ₃ Nanolaminates. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P501-P508.	0.9	12
41	Hafnium Oxide/Graphene/Hafnium Oxide-Stacked Nanostructures as Resistive Switching Media. <i>ACS Applied Nano Materials</i> , 2021, 4, 5152-5163.	2.4	12
42	Electric and Magnetic Properties of Atomic Layer Deposited ZrO ₂ -HfO ₂ Thin Films. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, N117-N122.	0.9	11
43	Memory Maps: Reading RRAM Devices without Power Consumption. <i>ECS Transactions</i> , 2018, 85, 201-205.	0.3	11
44	Current Pulses to Control the Conductance in RRAM Devices. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 291-296.	1.2	11
45	Influence of refilling effects on deep-level transient spectroscopy measurements in Se-doped Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1992, 72, 525-530.	1.1	10
46	Deep-level transient spectroscopy and electrical characterization of ion-implanted p-n junctions into undoped InP. <i>Journal of Applied Physics</i> , 1995, 78, 5325-5330.	1.1	10
47	Influence of electron cyclotron resonance nitrogen plasma exposure on the electrical characteristics of SiN _x :H/InP structures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 186.	1.6	10
48	Experimental investigation of the electrical properties of atomic layer deposited hafnium-rich silicate films on n-type silicon. <i>Journal of Applied Physics</i> , 2006, 100, 094107.	1.1	10
49	A detailed analysis of the energy levels configuration existing in the band gap of supersaturated silicon with titanium for photovoltaic applications. <i>Journal of Applied Physics</i> , 2015, 118, 245704.	1.1	10
50	Experimental Observation of Negative Susceptance in HfO ₂ -Based RRAM Devices. <i>IEEE Electron Device Letters</i> , 2017, 38, 1216-1219.	2.2	10
51	Electrical characteristics of anodic tantalum pentoxide thin films under thermal stress. <i>Microelectronics Reliability</i> , 2000, 40, 659-662.	0.9	9
52	Tantalum pentoxide obtained from Ta _x N and TaSi ₂ anodisation: an inexpensive and thermally stable high k dielectric. <i>Solid-State Electronics</i> , 2001, 45, 1441-1450.	0.8	9
53	Comparative Study of Flatband Voltage Transients on High-k Dielectric-Based Metal-Insulator-Semiconductor Capacitors. <i>Journal of the Electrochemical Society</i> , 2008, 155, G241.	1.3	9
54	Comparison between the electrical properties of atomic layer deposited thin ZrO ₂ films processed from cyclopentadienyl precursors. <i>Microelectronic Engineering</i> , 2009, 86, 1689-1691.	1.1	9

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55	Electrical Characterization of Defects Created by $\hat{\text{I}}^3$ -Radiation in HfO ₂ -Based MIS Structures for RRAM Applications. Journal of Electronic Materials, 2018, 47, 5013-5018.	1.0	9
56	Influences of the Temperature on the Electrical Properties of HfO ₂ -Based Resistive Switching Devices. Electronics (Switzerland), 2021, 10, 2816.	1.8	9
57	2 MeV electron irradiation effects on bulk and interface of atomic layer deposited high-k gate dielectrics on silicon. Thin Solid Films, 2013, 534, 482-487.	0.8	8
58	Advances towards 4J lattice-matched including dilute nitride subcell for terrestrial and space applications. , 2016, , .		8
59	Atomic Layer Deposition and Performance of ZrO ₂ -Al ₂ O ₃ Thin Films. ECS Journal of Solid State Science and Technology, 2018, 7, P287-P294.	0.9	8
60	Electrical and magnetic properties of atomic layer deposited cobalt oxide and zirconium oxide nanolaminates. Thin Solid Films, 2019, 669, 294-300.	0.8	8
61	Electrical characterization of electron cyclotron resonance deposited silicon nitride dual layer for enhanced Al/SiN _x :H/InP metal-insulator-semiconductor structures fabrication. Journal of Applied Physics, 1999, 86, 6924-6930.	1.1	7
62	Electrical Characterization of Al/SiN _x :H/n and p-In _{0.53} Ga _{0.47} As Structures by Deep-Level Transient Spectroscopy and Conductance Transient Techniques. Japanese Journal of Applied Physics, 2001, 40, 4479-4484.	0.8	7
63	Electrical characterization of hafnium oxide and hafnium-rich silicate films grown by atomic layer deposition. Microelectronics Reliability, 2005, 45, 949-952.	0.9	7
64	Identification of spatial localization and energetic position of electrically active defects in amorphous high-k dielectrics for advanced devices. Journal of Non-Crystalline Solids, 2008, 354, 393-398.	1.5	7
65	Influence of precursor chemistry and growth temperature on the electrical properties of SrTiO ₃ -based metal-insulator-metal capacitors grown by atomic layer deposition. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 01AC04.	0.6	7
66	The role of defects in solar cells: Control and detection defects in solar cells. , 2013, , .		7
67	Magnetic properties and resistive switching in mixture films and nanolaminates consisting of iron and silicon oxides grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	7
68	An experimental and simulation study of the role of thermal effects on variability in TiN/Ti/HfO ₂ /W resistive switching nonlinear devices. Chaos, Solitons and Fractals, 2022, 160, 112247.	2.5	7
69	Characterization of the EL2 center in GaAs by optical admittance spectroscopy. Journal of Applied Physics, 1990, 67, 6309-6314.	1.1	6
70	Detailed electrical characterization of DX centers in Se-doped Al _x Ga _{1-x} As. Journal of Applied Physics, 1997, 82, 4338-4345.	1.1	6
71	Electrical Characterization of Low Nitrogen Content Plasma Deposited and Rapid Thermal Annealed Al/SiN _x :H/InP Metal-Insulator-Semiconductor Structures. Japanese Journal of Applied Physics, 2000, 39, 6212-6215.	0.8	6
72	Experimental Verification of Direct Tunneling Assisted Electron Capture of Disordered-Induced Gap States in Metal-Insulator-Semiconductor Structures. Japanese Journal of Applied Physics, 2002, 41, L1215-L1217.	0.8	6

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73	Dynamics of set and reset processes on resistive switching memories. <i>Microelectronic Engineering</i> , 2019, 216, 111032.	1.1	6
74	Study of the set and reset transitions in HfO ₂ -based ReRAM devices using a capacitor discharge. <i>Solid-State Electronics</i> , 2021, 183, 108113.	0.8	6
75	Effect of Dielectric Thickness on Resistive Switching Polarity in TiN/Ti/HfO ₂ /Pt Stacks. <i>Electronics (Switzerland)</i> , 2022, 11, 479.	1.8	6
76	Deep levels in p+n junctions fabricated by rapid thermal annealing of Mg or Mg/P implanted InP. <i>Journal of Applied Physics</i> , 1997, 81, 3143-3150.	1.1	5
77	Thin film resistors and capacitors for advanced packaging. , 0, , .		5
78	Fabrication of Ta ₂ O ₅ Thin Films by Anodic Oxidation of Tantalum Nitride and Tantalum Silicide: Growing Mechanisms, Electrical Characterization and ULSI M-I-M Capacitor Performances. <i>Materials Research Society Symposia Proceedings</i> , 1999, 567, 371.	0.1	5
79	Selection of post-growth treatment parameters for atomic layer deposition of structurally disordered TiO ₂ thin films. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 404-408.	1.5	5
80	Interface quality of Sc ₂ O ₃ and Gd ₂ O ₃ films based metal-insulator-silicon structures using Al, Pt, and Ti gates: Effect of buffer layers and scavenging electrodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 01A106.	0.6	5
81	Atomic Layer Deposition and Characterization of Dysprosium-Doped Zirconium Oxide Thin Films. <i>Chemical Vapor Deposition</i> , 2015, 21, 181-187.	1.4	5
82	Scavenging effect on plasma oxidized Gd ₂ O ₃ grown by high pressure sputtering on Si and InP substrates. <i>Semiconductor Science and Technology</i> , 2015, 30, 035023.	1.0	5
83	Properties of atomic layer deposited iron oxide and bismuth oxide chloride structures. <i>Journal of Alloys and Compounds</i> , 2020, 846, 156099.	2.8	5
84	Silicon oxide-niobium oxide mixture films and nanolaminates grown by atomic layer deposition from niobium pentaethoxide and hexakis(ethylamino) disilane. <i>Nanotechnology</i> , 2020, 31, 195713.	1.3	5
85	Effective control of filament efficiency by means of spacer HfAlO _x layers and growth temperature in HfO ₂ based ReRAM devices. <i>Solid-State Electronics</i> , 2021, 183, 108085.	0.8	5
86	Constant-capacitance deep-level optical spectroscopy. <i>Solid-State Electronics</i> , 1989, 32, 287-293.	0.8	4
87	Title is missing!. <i>Journal of Materials Science: Materials in Electronics</i> , 2001, 12, 263-267.	1.1	4
88	Interfacial State Density and Conductance-Transient Three-Dimensional Profiling of Disordered-Induced Gap States on Metal Insulator Semiconductor Capacitors Fabricated from Electron-Cyclotron Resonance Plasma-Enhanced Chemical Vapor Deposited SiO _x NyHz Films. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 4978-4981.	0.8	4
89	Characterization of deep level defects present in mono-like, quasi-mono and multicrystalline silicon solar substrates. <i>Semiconductor Science and Technology</i> , 2015, 30, 035011.	1.0	4
90	Atomic Layer Deposition of Zirconium Dioxide from Zirconium Tetraiodide and Ozone. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P1-P8.	0.9	4

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91	Analysis of the performance of Nb ₂ O ₅ -doped SiO ₂ -based MIM devices for memory and neural computation applications. <i>Solid-State Electronics</i> , 2021, 186, 108114.	0.8	4
92	Structure and behavior of ZrO ₂ -graphene-ZrO ₂ stacks. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, 063411.	0.9	4
93	Dopant level freeze-out and nonideal effects in 6H-SiC epilayer junctions. <i>Journal of Applied Physics</i> , 1996, 79, 310-315.	1.1	3
94	Title is missing!. <i>Journal of Materials Science: Materials in Electronics</i> , 1999, 10, 373-377.	1.1	3
95	Charge and current hysteresis in dysprosium-doped zirconium oxide thin films. <i>Microelectronic Engineering</i> , 2015, 147, 55-58.	1.1	3
96	Magnetic and Electrical Performance of Atomic Layer Deposited Iron Erbium Oxide Thin Films. <i>ACS Omega</i> , 2017, 2, 8836-8842.	1.6	3
97	Study of the Influence of the Dielectric Composition of Al/Ti/ZrO ₂ :Al ₂ O ₃ /TiN/Si/Al Structures on the Resistive Switching Behavior for Memory Applications. <i>ECS Transactions</i> , 2018, 85, 143-148.	0.3	3
98	Control of the set and reset voltage polarity in anti-series and anti-parallel resistive switching structures. <i>Microelectronic Engineering</i> , 2019, 216, 111083.	1.1	3
99	Ability of capacitance-voltage transient technique to study spatial distribution and electric field dependence of emission properties of deep levels in semiconductors. <i>Materials Science and Technology</i> , 1995, 11, 1074-1078.	0.8	2
100	Electrical characterization of deep levels existing in Mg-Si- and Mg-P-Si-implanted n InP junctions. <i>Semiconductor Science and Technology</i> , 1998, 13, 389-393.	1.0	2
101	DLTS and conductance transient investigation on defects in anodic tantalum pentoxide thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2001, 12, 317-321.	1.1	2
102	A comparative study of anodic tantalum pentoxide and high-pressure sputtered titanium oxide. <i>Journal of Materials Science: Materials in Electronics</i> , 2003, 14, 375-378.	1.1	2
103	Electrical characterization of atomic-layer-deposited hafnium silicate for alternative gate dielectric application. , 0, , .		2
104	Electrical characterization of high-pressure reactive sputtered ScOx films on silicon. <i>Thin Solid Films</i> , 2011, 519, 2268-2272.	0.8	2
105	Electrical properties of intermediate band (IB) silicon solar cells obtained by titanium ion implantation. <i>AIP Conference Proceedings</i> , 2012, , .	0.3	2
106	Hole trap distribution on 2-MeV electron irradiated high-k dielectrics. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 032201.	0.6	2
107	Electrical Characterization of Amorphous Silicon MIS-Based Structures for HIT Solar Cell Applications. <i>Nanoscale Research Letters</i> , 2016, 11, 335.	3.1	2
108	Properties of Zirconium Oxide and Cobalt Ferrite Layered Nanocomposite. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P886-P892.	0.9	2

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109	The Role of Defects in the Resistive Switching Behavior of Ta ₂ O ₅ -TiO ₂ -Based Metal-Insulator-Metal (MIM) Devices for Memory Applications. <i>Journal of Electronic Materials</i> , 2018, 47, 4938-4943.	1.0	2
110	Energy Levels of Defects Created in Silicon Supersaturated with Transition Metals. <i>Journal of Electronic Materials</i> , 2018, 47, 4993-4997.	1.0	2
111	Resistive Switching Properties of Atomic Layer Deposited ZrO ₂ -HfO ₂ Thin Films. , 2018, , .		2
112	Single and complex devices on three topological configurations of HfO ₂ based RRAM. , 2020, , .		2
113	Atomic layer deposited nanolaminates of zirconium oxide and manganese oxide from manganese(III)acetylacetonate and ozone. <i>Nanotechnology</i> , 2021, 32, 335703.	1.3	2
114	Performance Assessment of Amorphous HfO ₂ -Based RRAM Devices for Neuromorphic Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 083002.	0.9	2
115	Structure and Electrical Behavior of Hafnium-Praseodymium Oxide Thin Films Grown by Atomic Layer Deposition. <i>Materials</i> , 2022, 15, 877.	1.3	2
116	Thermal emission processes of DX centres in Al _x Ga _{1-x} As:Si. <i>Solid-State Electronics</i> , 1997, 41, 103-109.	0.8	1
117	Electrical characterization of a He ion implantation-induced deep level existing in p+n InP junctions. <i>Journal of Applied Physics</i> , 1999, 85, 7978-7980.	1.1	1
118	Title is missing!. <i>Journal of Materials Science: Materials in Electronics</i> , 2003, 14, 287-290.	1.1	1
119	Conductance Transient Comparative Analysis of Electron-Cyclotron Resonance Plasma-Enhanced Chemical Vapor Deposited SiN _x , SiO ₂ /SiN _x and SiO _x N _y Dielectric Films on Silicon Substrates. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 66-70.	0.8	1
120	On the influence of substrate cleaning method and rapid thermal annealing conditions on the electrical characteristics of Al/SiN _x /SiO ₂ /Si fabricated by ECR-CVD. <i>Microelectronics Reliability</i> , 2005, 45, 978-981.	0.9	1
121	Electrical Characterization of High-Pressure Reactive Sputtered Sc ₂ O ₃ Films on Silicon. <i>ECS Transactions</i> , 2010, 28, 287-297.	0.3	1
122	Electrical Characterization of High-K Dielectric Gates for Microelectronic Devices. , 2012, , .		1
123	Deep level defects on mono-like and polycrystalline silicon solar cells. , 2013, , .		1
124	Resistive Switching Behavior and Electrical Properties of TiO ₂ :Ho ₂ O ₃ and HoTiO _x Based MIM Capacitors. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1691, 43.	0.1	1
125	Conduction and stability of holmium titanium oxide thin films grown by atomic layer deposition. <i>Thin Solid Films</i> , 2015, 591, 55-59.	0.8	1
126	Double Swing Quiescent-Current: An Experimental Detection Method of Ferroelectricity in Very Leaky Dielectric Films. <i>ECS Transactions</i> , 2020, 97, 3-6.	0.3	1

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127	(Invited) Current and Voltage Control of Intermediate States in Bipolar Rram Devices for Neuristor Applications. ECS Transactions, 2020, 97, 17-20.	0.3	1
128	DISORDERED STRUCTURE AND DENSITY OF GAP STATES IN HIGH-PERMITTIVITY THIN SOLID FILMS. , 2006, , 123-134.		1
129	Empirical Characterization of ReRAM Devices Using Memory Maps and a Dynamic Route Map. Electronics (Switzerland), 2022, 11, 1672.	1.8	1
130	Conductance Transients Study of Slow Traps in Al/SiNx:H/Si and Al/SiNx:H/InP Metal-Insulator-Semiconductor Structures. Materials Research Society Symposia Proceedings, 1997, 500, 87.	0.1	0
131	Electrical characterization of He-ion implantation-induced deep levels in p+n InP junctions. Journal of Applied Physics, 1999, 86, 4855-4860.	1.1	0
132	Title is missing!. Journal of Materials Science: Materials in Electronics, 1999, 10, 413-418.	1.1	0
133	Conductance-transient three-dimensional profiling of disordered induced gap states on metal-insulator-semiconductor structures. Materials Research Society Symposia Proceedings, 2001, 699, 441.	0.1	0
134	Radio-Frequency Impedance Analysis of Anodic Tantalum Pentoxide Thin Films. Materials Research Society Symposia Proceedings, 2001, 699, 651.	0.1	0
135	On the interface quality of MIS structures fabricated from Atomic Layer Deposition of HfO ₂ , Ta ₂ O ₅ and Nb ₂ O ₅ Ta ₂ O ₅ Nb ₂ O ₅ dielectric thin films. Materials Research Society Symposia Proceedings, 2003, 786, 3181.	0.1	0
136	Conductance transient comparative analysis of ECR-PECVD deposited SiNx, SiO ₂ /SiNx and SiOxNy dielectric films on silicon substrates. Materials Research Society Symposia Proceedings, 2003, 786, 3121.	0.1	0
137	A comparative study of atomic layer deposited advanced high-k dielectrics. , 2005, , .		0
138	Interface quality of high-pressure reactive sputtered and atomic layer deposited titanium oxide thin films on silicon. , 0, , .		0
139	Electrical Characterization of High-k Dielectrics by Means of Flat-Band Voltage Transient Recording. Materials Research Society Symposia Proceedings, 2007, 996, 1.	0.1	0
140	Electrical characterization of high-k based MIS capacitors using flat-band voltage transients. , 2009, , .		0
141	Study of Atomic Layer Deposited Zirconium Oxide Thin Films by Using Mono-Cyclopentadienyl Based Precursors. , 2009, , .		0
142	Effect of interlayer trapping and detrapping on the determination of interface state densities on high-k dielectric stacks. , 2009, , .		0
143	Electrical characterization of ZrO ₂ -based MIS structures with highly doped Si substrates. , 2009, , .		0
144	A study of tunneling assisted charge exchange on the inner interface of high-k dielectric stacks. , 2011, , .		0

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145	Characterization of SrTiO ₃ -based MIM capacitors grown by using different precursors and growth temperatures. , 2011, , .		0
146	Negative-resistance effect in Al ₂ O ₃ based and nanolaminated MIS structures. , 2011, , .		0
147	Electron Irradiation Effects on Atomic Layer Deposited High-k Gate Dielectrics. ECS Transactions, 2011, 41, 349-359.	0.3	0
148	Electrical study of ScO-based MIS structures using Al and Ti as gate electrodes. , 2013, , .		0
149	Photocurrent measurements for solar cells characterization. , 2013, , .		0
150	Single-parameter model for the post-breakdown conduction characteristics of HoTiOx-based MIM capacitors. Microelectronics Reliability, 2014, 54, 1707-1711.	0.9	0
151	Electrical characterization of MIS capacitors based on Dy ₂ O ₃ -doped ZrO ₂ dielectrics. , 2015, , .		0
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